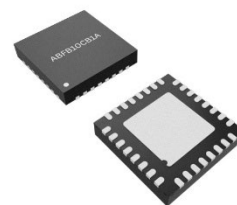


Ten LVCMOS Output Low Additive Jitter Fanout Buffer

Description

The Abracon ABFB10CB1A series is a clock buffer, offering ten LVCMOS outputs and is available in a 32-pin 5mm x 5mm x 0.9mm VQFN package. This series features a wide frequency range from 0MHz to 200MHz, low output skew, and ultra-low additive jitter. The ABFB10CB1A series supports 1.5V, 1.8V, 2.5V, or 3.3V supply voltage on the LVCMOS outputs, and its operation is ensured over the industrial temperature range -40°C to +85°C.



Features

- 3-to-1 Input Multiplexer: Two Inputs Accept Any Differential (LVPECL, HCSL, LVDS, SSTL, CML, LVCMOS) or a Single Ended Signal and the Third Input Accepts a Crystal or a Single Ended Signal
- Ten 1.5V/1.8V/2.5V/3.3V LVCMOS Outputs
- Supports Frequencies from 0 MHz to 200 MHz
- Supports Crystals from 8 MHz to 60 MHz
- Ultra-Low Additive Jitter: 17 fs (12 kHz to 20 MHz)
- Ultra-Low Noise Floor of -170 dBc/Hz
- Supports 2.5V or 3.3V Power Supplies
- Output to Output Skew of 30 ps (Typical)
- Input to Output Delay of 2 ns (Typical)
- [REACH/RoHS II Compliant](#) | [MSL Level 3](#)

Typical Applications

- General Purpose Clock Distribution
- Low Jitter Clock Trees
- Logic Translation
- Clock and Data Signal Restoration
- Wired and Wireless Communications
- High Performance Microprocessor Clock Distribution
- Medical Imaging
- Test Equipment

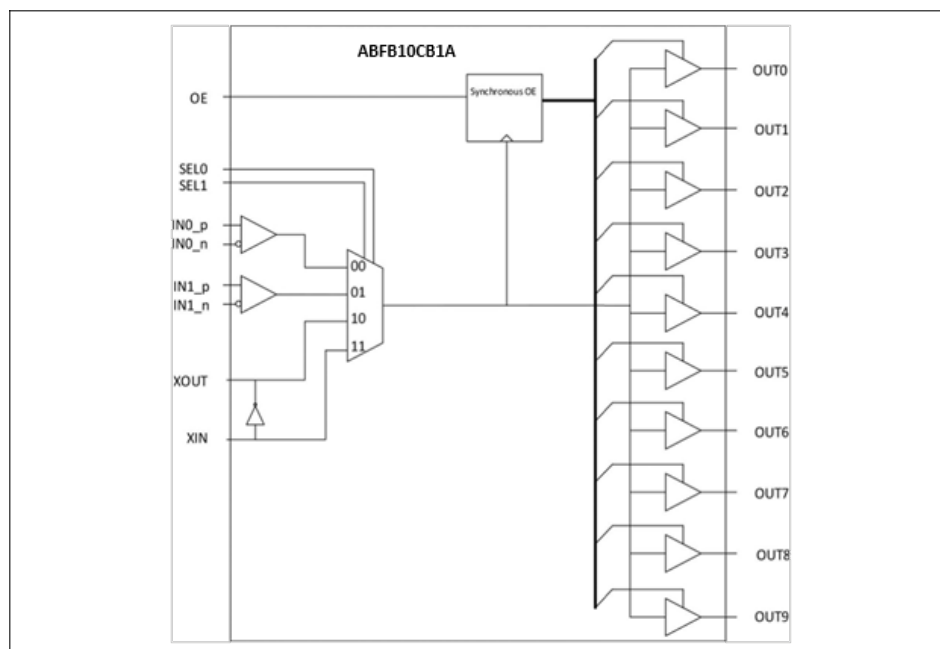


FIGURE 0.1: Functional Block Diagram

1

Packaging
Blank: Bulk
T: 490/tray
T4: 4000/reel (12mm pocket pitch)

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1.0 PIN DESCRIPTION AND CONFIGURATION

The device is packaged in a 5 mm × 5 mm 32-lead VQFN.

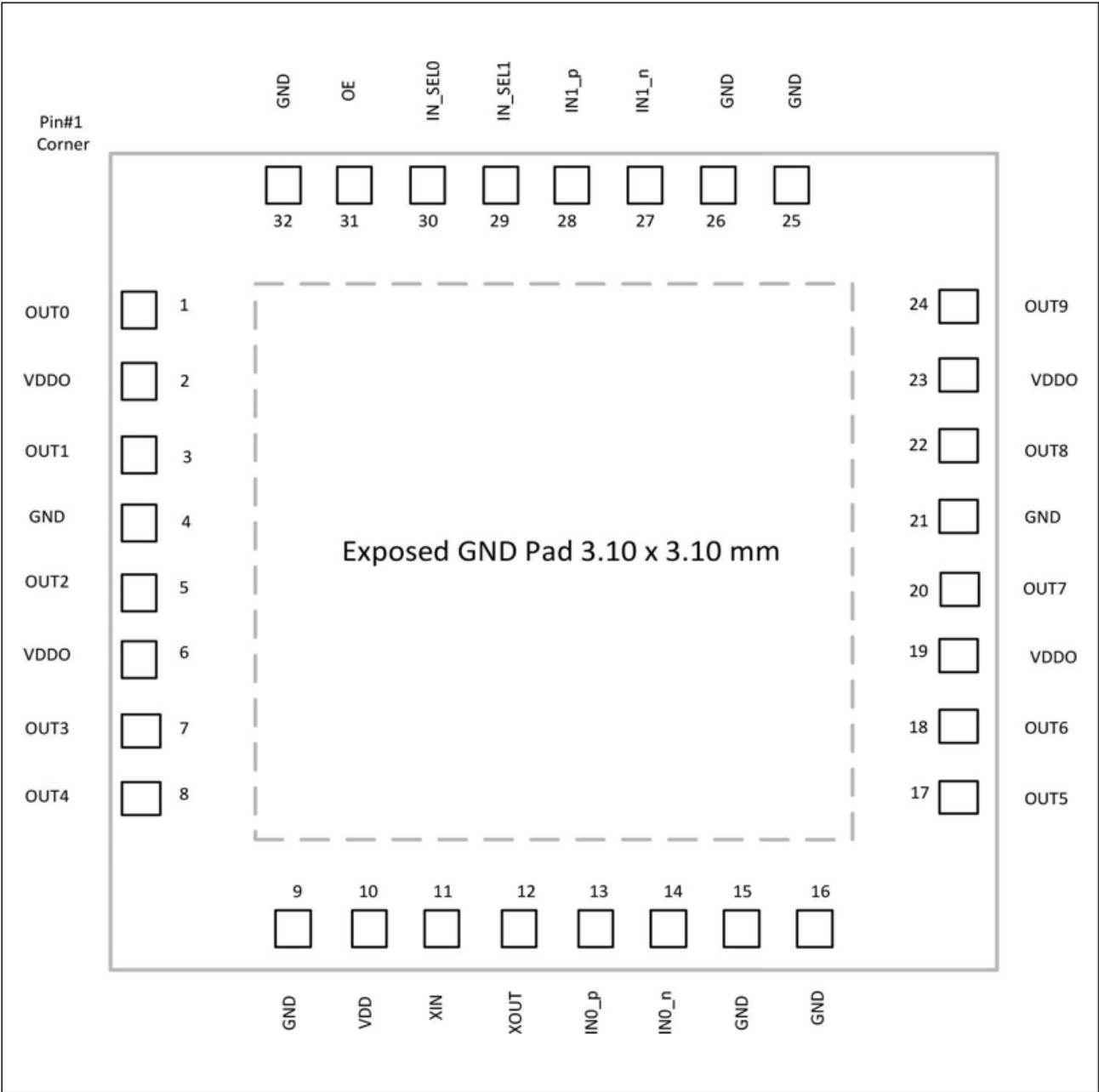


FIGURE 1.1: 32-Lead 3.10 mm × 3.10 mm VQFN with E-Pad.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

All device inputs and outputs are LVPECL unless described otherwise. The I/O column uses the following symbols: I – input, IPU – input with 300 k Ω internal pull-up resistor, IPD – input with 300 k Ω internal pull-down resistor, IAPU – input with 30 k Ω internal pull-up resistor, IAPD – input with 30 k Ω internal pull-down resistor, IAPU/APD – input biased at VDD/2 with 60 k Ω internal pull-up and 60 k Ω pull-down resistors, O – output, I/O – Input/Output pin, P – power supply pin.

TABLE 1.1: PIN DESCRIPTION

Pin Number	Pin Name	Type	Description		
Input Reference					
13	IN0_p	I _{APD}	Input Differential or Single-Ended References 0 and 1		
14	IN0_n	I _{APU/APD}			
28	IN1_p	I _{APD}			
27	IN1_n	I _{APU/APD}	Input frequency range 0 Hz to 200 GHz.		
			Non-inverting inputs (_p) are pulled down with internal 30 kΩ pull-down resistors. Inverting inputs (_n) are pulled up and pulled down with 60 kΩ internal resistors (30 kΩ equivalent) to keep inverting input voltages at VDD/2 when inverting inputs are left floating (device fed with a single-ended reference).		
Output Clocks					
1	OUT0	O	Ultra Low Additive Jitter LVCMOS Outputs 0 to 9		
3	OUT1				
5	OUT2				
7	OUT3				
8	OUT4				
17	OUT5				
18	OUT6				
20	OUT7				
22	OUT8				
24	OUT9				
Control					
30 29	IN_SEL0 IN_SEL1	I _{PD}	Input Select Pins. Logic level on these pins selects which input will be passed to the output.		
			IN_SEL1	IN_SEL0	OUTN
			0	0	Input 0 (IN0)
			0	1	Input 1 (IN1)
			1	0	Crystal Oscillator or Overdrive
		1	1	Crystal Bypass	
31	OE	I _{PD}	Output Enable. When high outputs are enabled. When low outputs are high-Z.		
Crystal Oscillator					
11	XIN	I	Crystal Oscillator Input or Crystal Bypass Mode or Crystal Overdrive Mode. If crystal oscillator is not used pull down this pin or connect it to ground.		
12	XOUT	O	Crystal Oscillator Output.		
Power and Ground					
10	VDD	P	Positive Supply Voltage. Connect to 3.3V or 2.5V supply. VDD voltage must be higher or equal to VDDO.		

TABLE 1.1: PIN DESCRIPTION (CONTINUED)

Pin Number	Pin Name	Type	Description
2	VDDO	P	Positive Supply Voltage for LVCMOS Outputs. Connect 3.3V, 2.5V, 1.8V or 1.5V power supply.
6			
19			
23			
4	GND	P	Ground. Connect to ground.
9			
15			
16			
21			
25			
26			
32	E-Pad		
E-Pad			

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

2.0 FUNCTIONAL DESCRIPTION

The device is a programmable or hardware pin controlled low additive jitter, low power 3×10 LVCMOS fanout buffer.

Two inputs can accept signal in differential (LVPECL, SSTL, LVDS, HSTL, CML) or single ended (LVPECL or LVCMOS) format and the third input can accept a single ended signal or it can be used to build a crystal oscillator by connecting an external crystal resonator between its XIN and XOUT pins.

The device has ten LVCMOS outputs which can be powered from 3.3V, 2.5V, 1.8V, or 1.5V supply. Output can be synchronously enabled/disabled via OE pin.

The device operates from 2.5V $\pm$ 5% or 3.3V $\pm$ 5% supply. Its operation is guaranteed over the industrial temperature range -40°C to +85°C.

2.1 Clock Inputs

The following block diagrams show how to terminate different signals fed to the device inputs. Figure 2.1 shows how to terminate a single ended output such as LVCMOS. Ideally, resistors R1 and R2 should be 100 Ω each so that the transmission line is terminated with matched impedance (50 Ω). However, if the driving strength of the output driver is not sufficient resistor values should be increased.

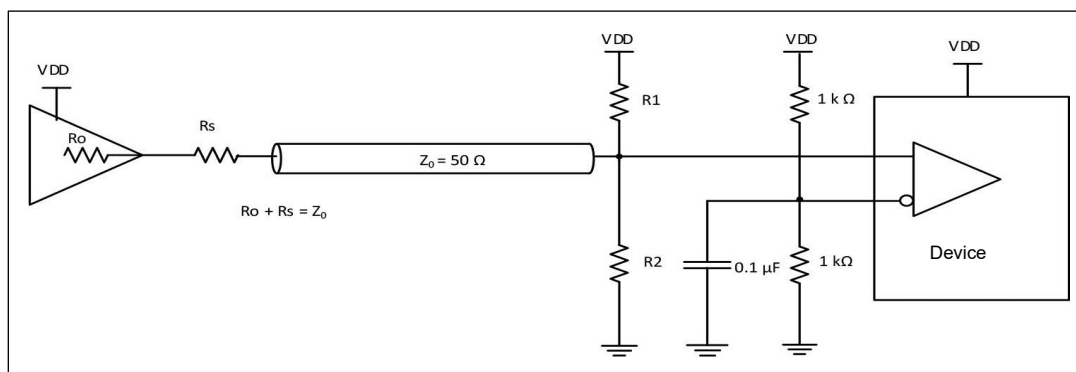


FIGURE 2.1: Input Driven by a Single-Ended Output.

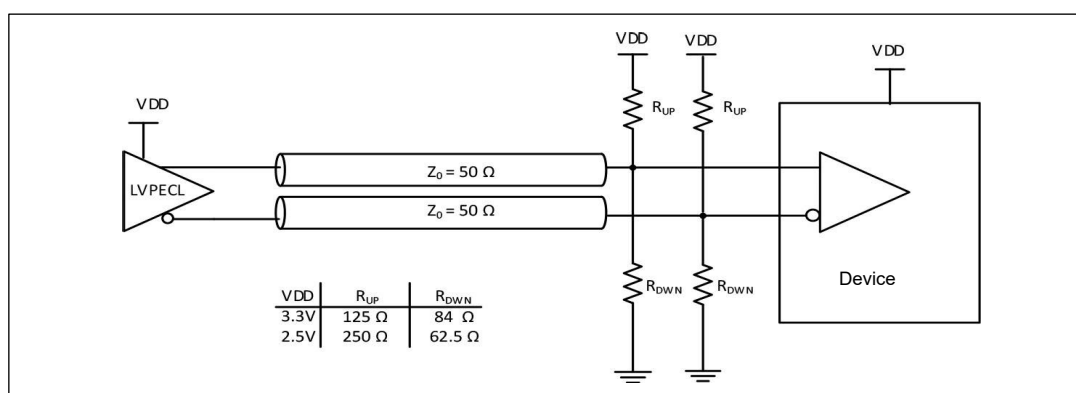


FIGURE 2.2: Input Driven by DC-Coupled LVPECL Output.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

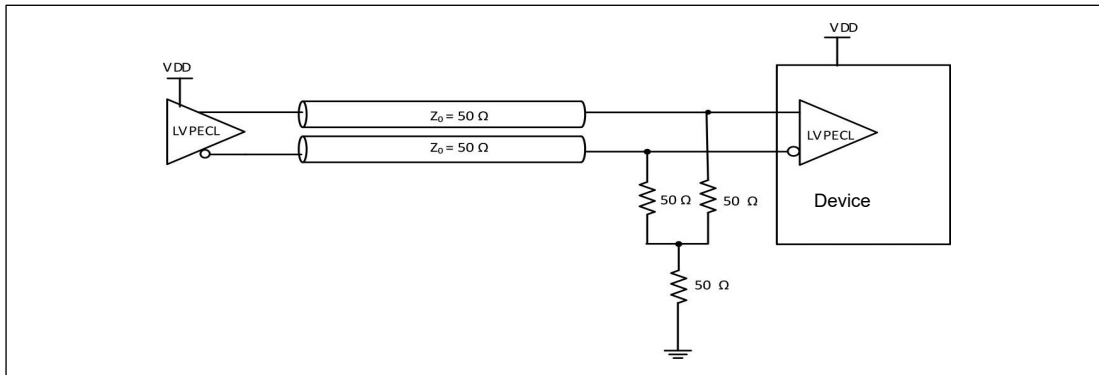


FIGURE 2.3: Input Driven by DC-Coupled LVPECL Output (Alternative Termination).

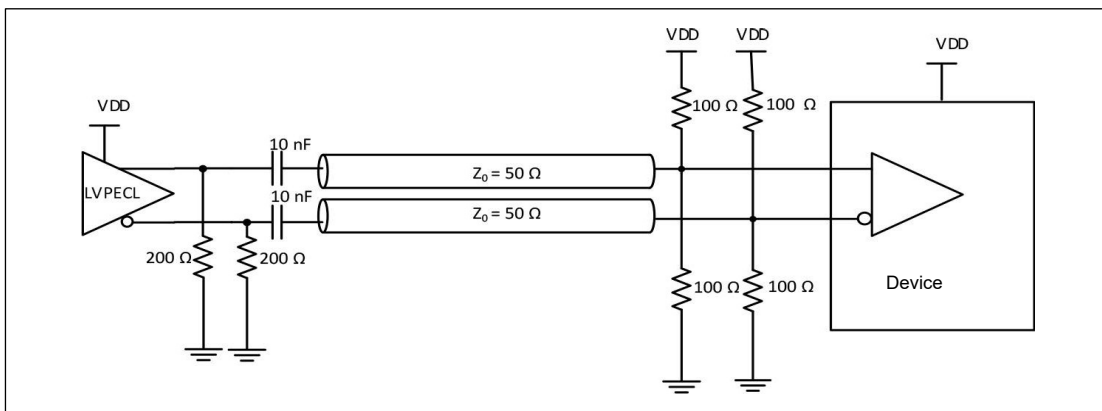


FIGURE 2.4: Input Driven by AC-Coupled LVPECL Output.

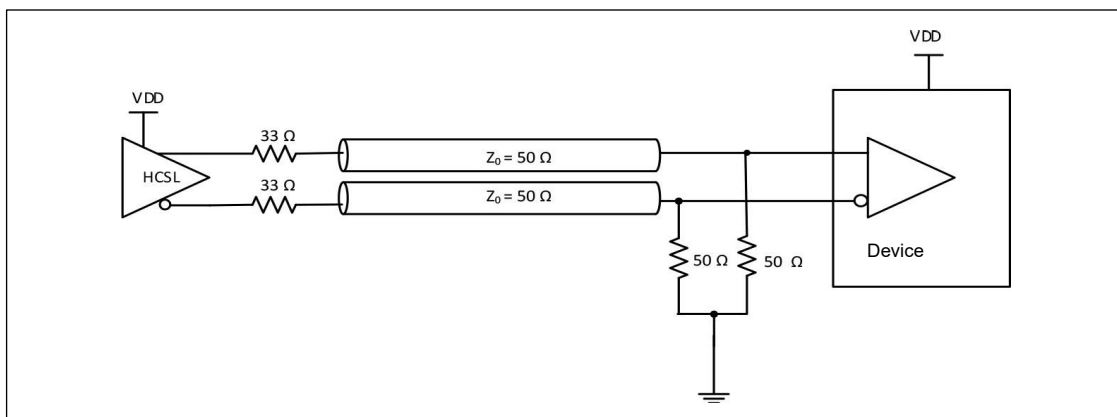


FIGURE 2.5: Input Driven by HCSL Output.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

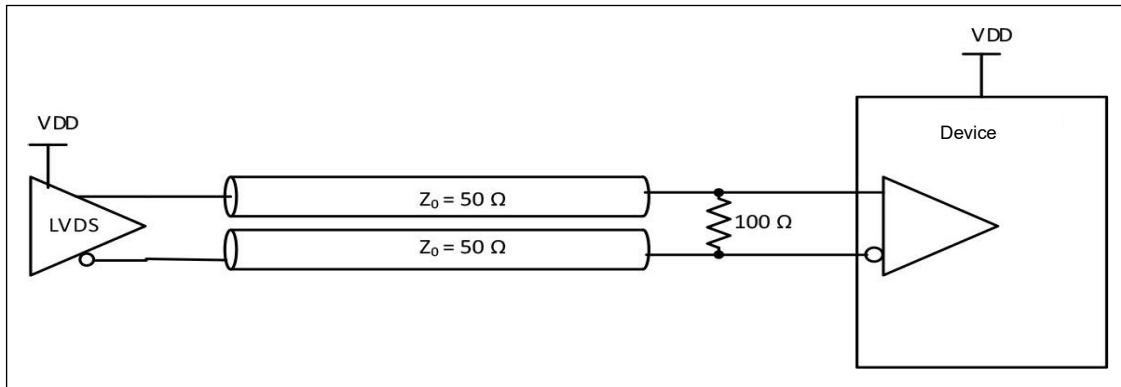


FIGURE 2.6: Input Driven by LVDS Output.

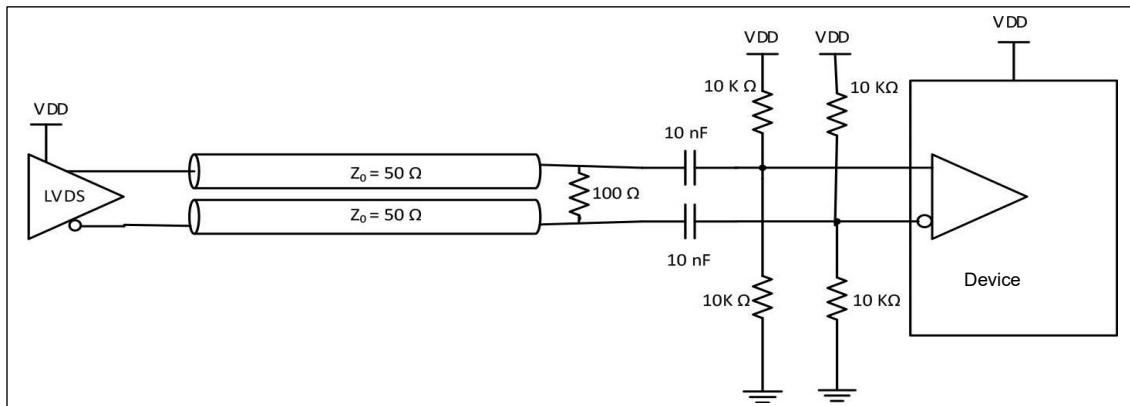


FIGURE 2.7: Input Driven by AC-Coupled LVDS.

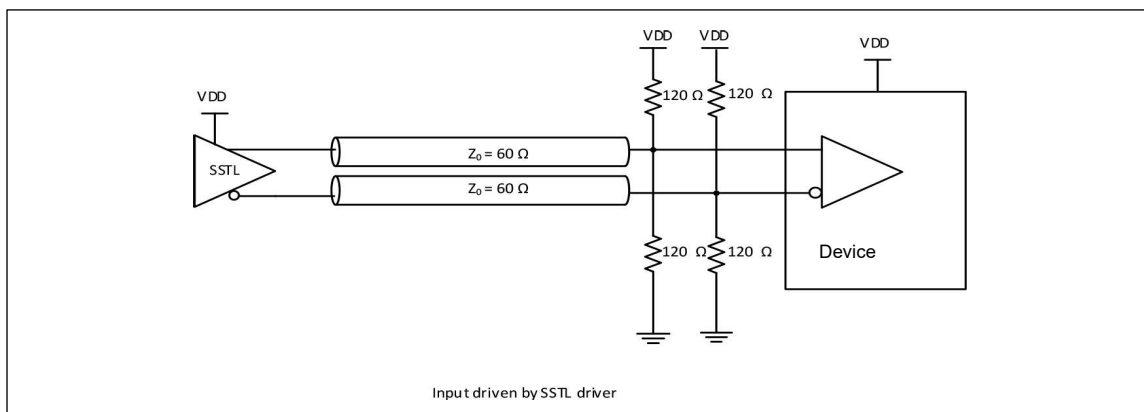


FIGURE 2.8: Input Driven by an SSTL Output.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

2.2 Clock Outputs

LVCMOS outputs require only series termination resistor whose value is depending on LVCMOS output voltage as shown in Figure 2.9.

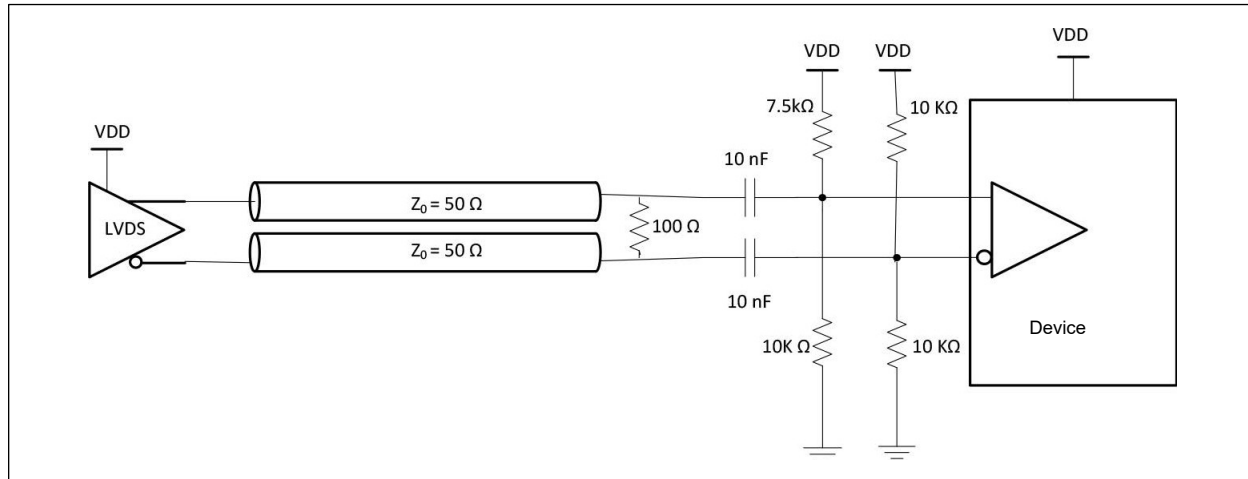


FIGURE 2.9: Termination for LVCMOS Outputs.

2.3 Crystal Oscillator Input

The crystal oscillator circuit can work with crystal resonators from 8 MHz to 160 MHz. Load capacitors C1 and C2 shall be selected as per crystal vendor recommendation. Shunt resistor is implemented inside the device. If the crystal is not used, connect XIN pin to ground.

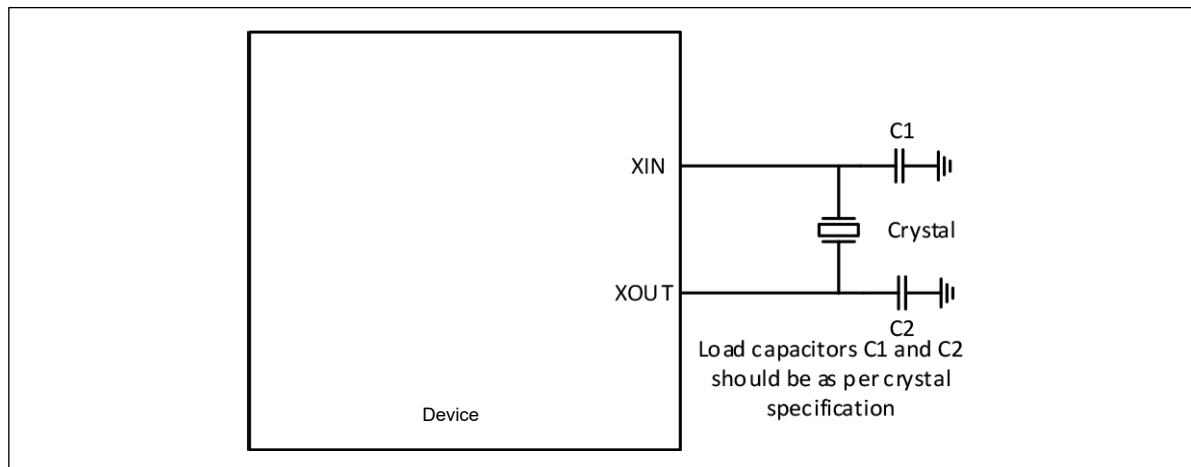


FIGURE 2.10: Crystal Oscillator Circuit in Hardware Controlled Mode.

The phase noise plot for 25 MHz crystal is shown in Figure 2.11. The phase noise floor of the device is below 170 dBc/Hz as can be seen on the figure.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

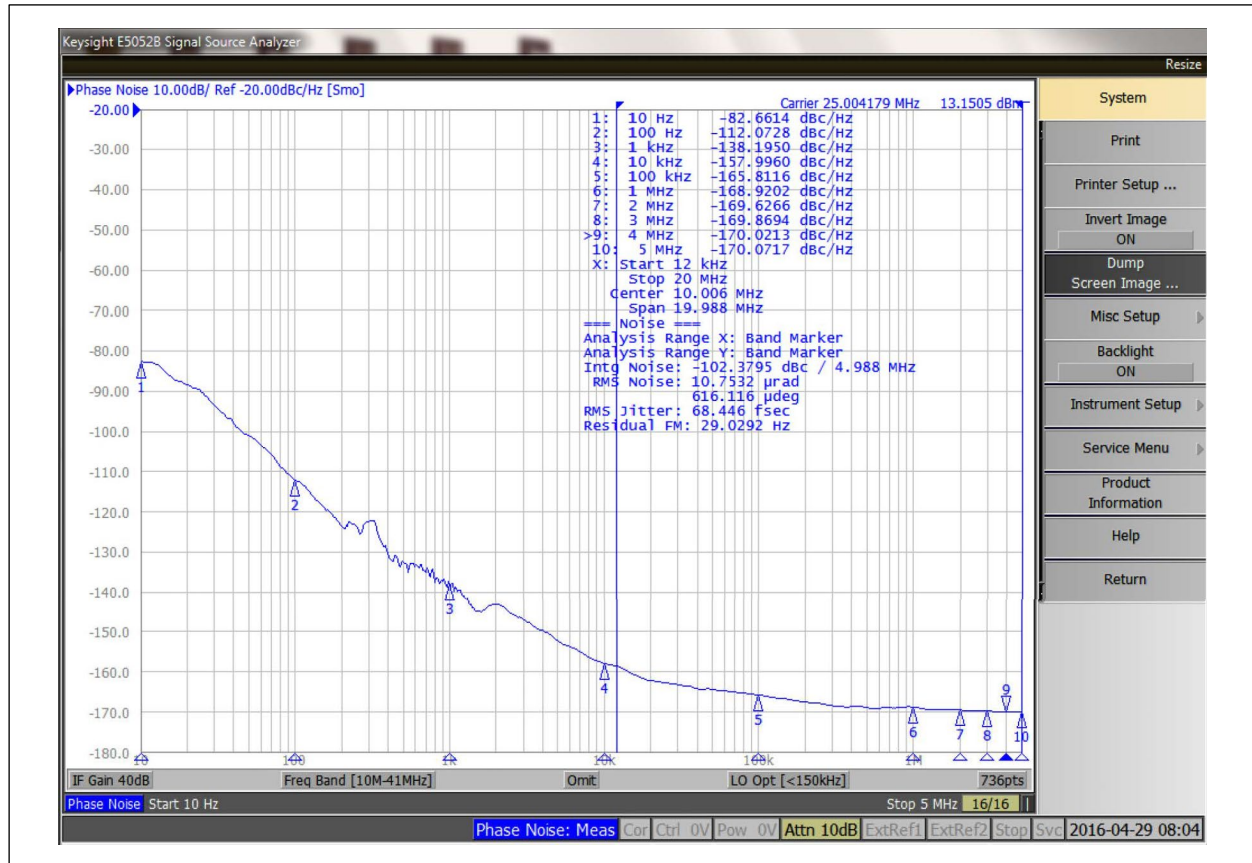


FIGURE 2.11: Phase Noise Plot with 25 MHz Crystal.

2.4 Termination of Unused Inputs and Outputs

Unused inputs can be left unconnected or alternatively IN_0/1 can be pulled-down by 1 K Ω resistor. Unused outputs should be left unconnected.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

2.5 Power Consumption

The total device power consumption can be calculated as:

EQUATION 2-1:

$$P_T = P_S + P_{XTAL} + P_C + P_D$$

Where:

$P_S = V_{DD} \times I_S$	This is static power consumed by input buffers. If XTAL is running, this power should be set to zero. The static current (I_S) is specified in Table 3.2 .
$P_{XTAL} = V_{DD} \times I_{DD_XTAL}$	This is the power consumption of the XTAL circuit. The current of the XTAL circuit is provided in Table 3.2 . If XTAL is not used, the power consumption is equal to zero.
$P_C = V_{DDO} \times I_{DDC}$	Common output power shared among all ten outputs. The current I_{DDC} is specified in Table 3.2 .
$P_D = V_{DDO} \times (I_{DD} \times n \times f / 100 \text{ MHz} + V_{DD} \times C_{LOAD} \times f \times n)$	Dynamic power where dynamic current (I_{DD}) is specified in Table 3.2 . C_{LOAD} is capacitive load driven by an output, f is frequency of the output clock and n is number of active outputs.

The power consumption for different clock frequencies and power supply voltages can be quickly estimated from [Figure 2.12](#), [Figure 2.13](#), and [Figure 2.14](#).

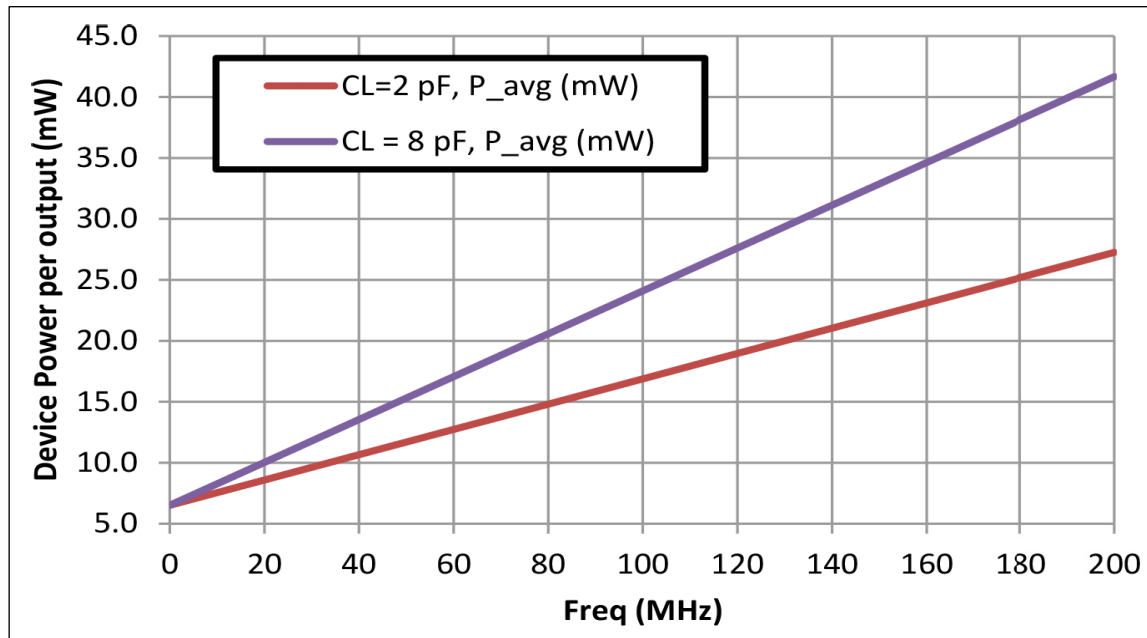
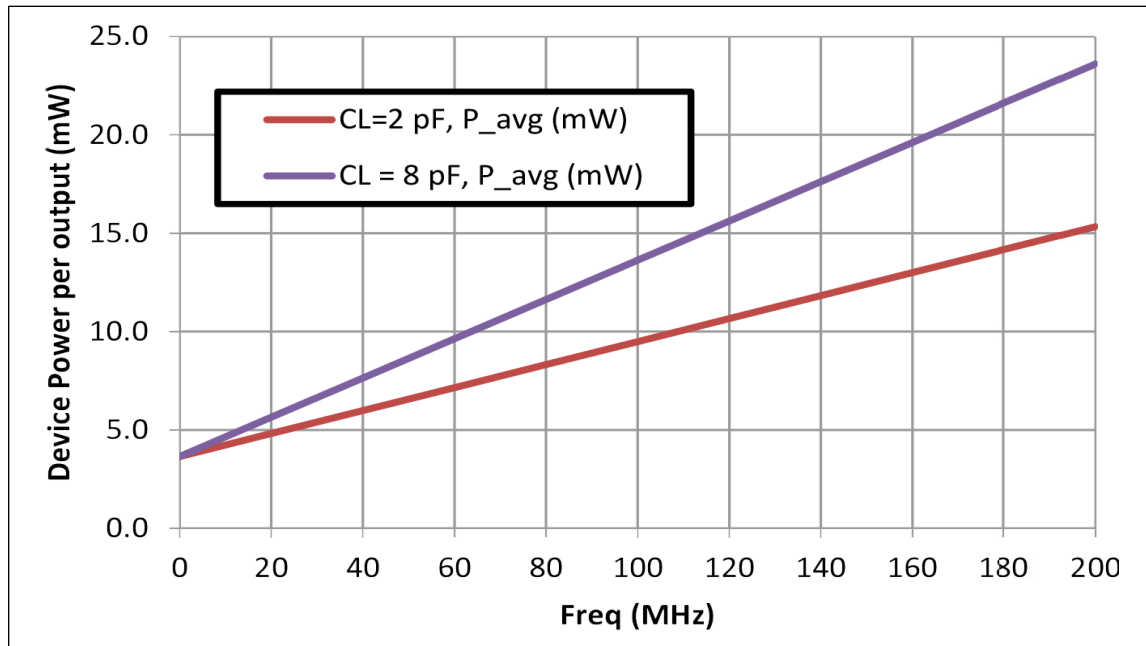
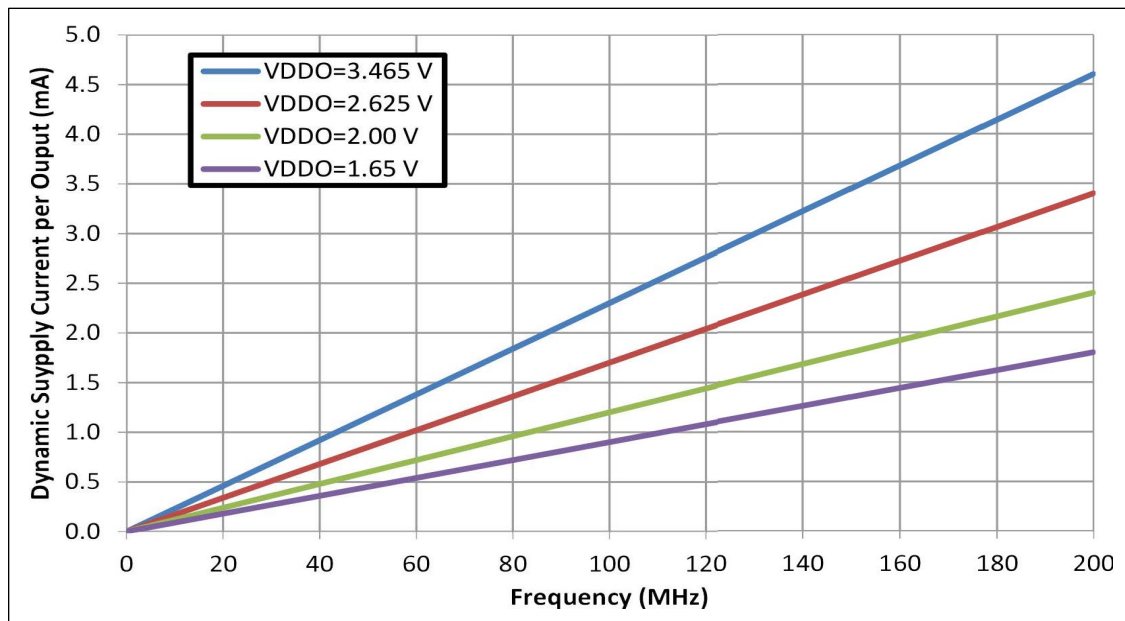


FIGURE 2.12: Device Power Consumption per Output for $V_{DD} = V_{DDO} = 3.465V$.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

**FIGURE 2.13: Device Power Consumption per Output for $V_{DD} = V_{DDO} = 2.625V$.****FIGURE 2.14: Dynamic Supply Current per Output for Different Output Supply Voltages.**

2.6 Power Supply Filtering

Each power pin (VDD and VDDO) should be decoupled with 0.1 μF capacitor with minimum equivalent series resistance (ESR) and minimum series inductance (ESL). For example, 0402 X5R Ceramic Capacitors with 6.3V minimum rating could be used. These capacitors should be placed as close as possible to the power pins. To reduce the power noise from adjacent digital components on the board, each power supply could be further insulated with low resistance ferrite bead with two capacitors. The ferrite bead will also insulate adjacent component from the noise generated from the device. Figure 2.15 shows the recommended decoupling for each power pin.

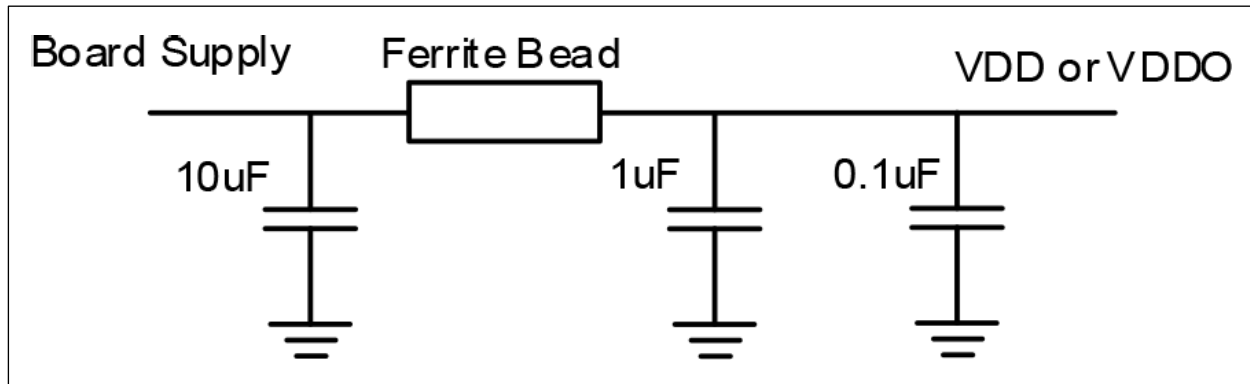


FIGURE 2.15: Power Supply Filtering.

2.7 Device Control

The device is controlled via Output Enable (OE) and Input Select (SEL0/1) input pins.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

3.0 ELECTRICAL CHARACTERISTICS**TABLE 3.1: ABSOLUTE MAXIMUM RATINGS (Note 1, Note 2, Note 3)**

Parameter	Symbol	Min.	Max.	Units.
Supply Voltage, 3.3V	V_{DD}/V_{DDO}	-0.5	+4.6	V
Supply Voltage, 2.5V	V_{DD}/V_{DDO}	-0.5	+4.6	V
Supply voltage, 1.8V	V_{DDO}	-0.5	+2.5	V
Supply voltage, 1.5V	V_{DDO}	-0.5	+2.0	V
Storage Temperature Range	T_{ST}	-55	+125.0	°C

Note 1: Exceeding these values may cause permanent damage.

Note 2: Functional operation under these conditions is not implied.

Note 3: Voltages are with respect to ground (GND) unless otherwise stated.

TABLE 3.2: RECOMMENDED OPERATING CONDITIONS (Note 1, Note 2)

Parameter	Symbol	Min.	Typ.	Max.	Units.
Supply Voltage, 3.3V	V_{DD}/V_{DDO}	3.135	3.300	3.465	V
Supply Voltage, 2.5V	V_{DD}/V_{DDO}	2.375	2.500	2.625	V
Supply Voltage, 1.8V	V_{DDO}	1.600	1.800	2.000	V
Supply Voltage, 1.5V	V_{DDO}	1.350	1.500	1.650	V
Operating Temperature	T_A	-40.000	+25.000	+85.000	°C
Input Voltage	V_{DD-IN}	-0.300	—	$V_{DD} + 0.300$	V

Note 1: Voltages are with respect to ground (GND) unless otherwise stated.

Note 2: The device supports two power supply modes (3.3V and 2.5V).

TABLE 3.3: CURRENT CONSUMPTION

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
Static device current	$I_{S_3.3V}$	—	15	18	mA	$V_{DD} = 3.465V$
	$I_{S_2.5V}$	—	12	15	mA	$V_{DD} = 2.625V$
Device current with 25 MHz XTAL input	$I_{DD_XTAL_3.3V}$	—	24	27	mA	$V_{DD} = 3.465V$
	$I_{DD_XTAL_2.5V}$	—	18	20	mA	$V_{DD} = 2.625V$
Dynamic current per output (f = 100MHz), Note 1, Note 2 Needs to be scaled for different frequencies by f/100 MHz, Driving Strength = 1 (registers 0x09, 0x0A)	$I_{DD_3.3V}$	—	4.2	4.7	mA	$V_{DD} = 3.465V$
	$I_{DD_2.5V}$	—	3.0	3.5	mA	$V_{DD} = 2.625V$
	$I_{DD_1.8V}$	—	2.1	2.4	mA	$V_{DD} = 2.000V$
	$I_{DD_1.5V}$	—	1.6	1.8	mA	$V_{DD} = 1.650V$
Dynamic current per output (f = 100MHz), Note 1, Note 2 Needs to be scaled for different frequencies by f/100 MHz, Driving Strength = 0 (registers 0x09, 0x0A)	$I_{DD_3.3V}$	—	2.3	3.0	mA	$V_{DD} = 3.465V$
	$I_{DD_2.5V}$	—	1.7	1.8	mA	$V_{DD} = 2.625V$
	$I_{DD_1.8V}$	—	1.2	1.3	mA	$V_{DD} = 2.000V$
	$I_{DD_1.5V}$	—	0.9	1.0	mA	$V_{DD} = 1.650V$
Common output current, Note 3	$I_{DD_3.3V}$	—	3.8	8.0	mA	$V_{DD} = 3.465V$
	$I_{DD_2.5V}$	—	1.9	3.3	mA	$V_{DD} = 2.625V$
	$I_{DD_1.8V}$	—	1.2	1.7	mA	$V_{DD} = 2.000V$
	$I_{DD_1.5V}$	—	1.0	1.4	mA	$V_{DD} = 1.650V$

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

Note 1: Needs to be scaled for different frequencies by $f/100$ MHz.

Note 2: To calculate total power consumption use following formula: $P = (I_S + I_{DD_XTAL}) \times V_{DD} + (I_{DDC} + I_{DD} \times n \times f/100 \text{ MHz} + V_{DDO} \times C_{LOAD} \times f \times n) \times V_{DDO}$, where I_{DD_XTAL} should be set to zero if XTAL is not used or I_S should be set to zero if XTAL is used. Also, n = number of active outputs; f = frequency of the clock; C_{LOAD} = capacitive load driven by an output.

Note 3: This current is consumed by device whenever one or more outputs are enabled. It is independent of the number of active outputs.

TABLE 3.4: INPUT CHARACTERISTICS (Note 1, Note 2)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
CMOS high-level input voltage for SPI_CLK, SPI_CS and SPI_SDI	V_{CIH}	1.20	—	—	V	—
CMOS low-level input voltage for SPI_CLK, SPI_CS and SPI_SDI	V_{CIL}	—	—	0.45	V	—
CMOS input leakage current for SPI_CLK, SPI_CS and SPI_SDI, Note 3	I_{IL}	−40	—	10	μA	$V_I = V_{DD}$ or 0 V
Differential input common mode voltage for IN0_p/n and IN1_p/n	V_{CM}	0.5	—	$V_{DD}-0.85$	V	—
Differential input voltage difference for IN0_p/n and IN1_p/n	V_{ID}	0.15	—	1.3	V	—
Differential input leakage current for IN0_p/n and IN1_p/n (includes current in pull-up and pull-down resistors), Note 4	I_{IL}	−200	—	100	μA	$V_I = V_{DD}$ or 0 V
Single ended input high voltage for IN_0_p and IN_1_p	V_{SIH}	2	—	$V_{DD} + 0.3$	V	$V_{DD} = 3.3V \pm 5\%$
		1.6	—	$V_{DD} + 0.3$	V	$V_{DD} = 2.5V \pm 5\%$
Single ended input low voltage for IN_0_p and IN_1_p	V_{SIL}	−0.3	—	1.3	V	$V_{DD} = 3.3V \pm 5\%$
		−0.3	—	0.9	V	$V_{DD} = 2.5V \pm 5\%$
Input frequency	f_{IN}	0	—	200	MHz	—
Input duty cycle (200 MHz Input Clock)	DC	35	—	65	%	Note 5
Input slew rate	slew	—	2	—	V/ns	—
Input pull-up/ pull-down resistance	R_{PU}/R_{PD}	—	60 kΩ	—	kΩ	—
Input pull-down resistance (INx_p)	R_{PD}	—	30 kΩ	—	kΩ	—

Note 1: Values are over recommended operating conditions.

Note 2: Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$).

Note 3: CMOS input leakage is due to 300 kΩ pull-up/pull-down resistors.

Note 4: Differential input leakage is due to 60 kΩ pull-up/pull-down resistors INx_n and due to 30 kΩ pull-down resistor for INx_p.

Note 5: Minimum and maximum duty cycles should be scaled for different input frequencies. For example, a 10 MHz input clock would have the minimum duty cycle of 2% and the maximum duty cycle of 98%.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

TABLE 3.5: CRYSTAL OSCILLATOR CHARACTERISTICS (Note 1)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
Mode of oscillation	mode	Fundamental			—	—
Frequency	f	8	—	160	MHz	—
On chip shunt resistor	R	—	0.5	—	MΩ	—
On chip capacitance	C	—	12	—	pF	—
Frequency in overdrive mode, Note 2	f _{OV}	0.1	—	200	MHz	Functional but may not meet AC parameters. Minimum depends on AC coupling. Capacitor (0.1 uF assumed).
Frequency in bypass mode, Note 3	f _{BP}	—	—	200	MHz	Functional but may not meet AC parameters.

Note 1: Values are over recommended operating conditions. Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$).

Note 2: Maximum input level is 2.0V.

Note 3: Maximum output level is V_{DD} .

TABLE 3.6: LVCMOS OUTPUT CHARACTERISTICS (Note 1)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
Output high voltage	V_{OH}	$0.8 \times V_{DDO}$	—	—	V	$V_{DDO} = 3.3V \pm 5\%$
		$0.8 \times V_{DDO}$	—	—	V	$V_{DDO} = 2.5V \pm 5\%$
		$0.7 \times V_{DDO}$	—	—	V	$V_{DDO} = 1.8V \pm 10\%$
		$0.7 \times V_{DDO}$	—	—	V	$V_{DDO} = 1.5V \pm 10\%$
Output low voltage	V_{OL}	—	—	$0.2 \times V_{DDO}$	V	$V_{DDO} = 3.3V \pm 5\%$
		—	—	$0.2 \times V_{DDO}$	V	$V_{DDO} = 2.5V \pm 5\%$
		—	—	$0.3 \times V_{DDO}$	V	$V_{DDO} = 1.8V \pm 10\%$
		—	—	$0.3 \times V_{DDO}$	V	$V_{DDO} = 1.5V \pm 10\%$
Output impedance	R_O	—	17	—	Ω	$V_{DDO} = 3.3V$
		—	21	—	Ω	$V_{DDO} = 2.5V$
		—	30	—	Ω	$V_{DDO} = 1.8V$
		—	42	—	Ω	$V_{DDO} = 1.5V$
Output slew rate, rise or fall (20% to 80%)	t_r, t_f	3.19	5.14	6.33	V/ns	$V_{DDO} = 3.3V \pm 5\%$
		1.72	3.74	4.61	V/ns	$V_{DDO} = 2.5V \pm 5\%$
		1.64	2.52	3.32	V/ns	$V_{DDO} = 1.8V \pm 10\%$
		1.20	1.96	2.54	V/ns	$V_{DDO} = 1.5V \pm 10\%$
Output frequency	F_O	0	—	200	MHz	—
Output duty cycle		50.26	—	53.18	%	Input. duty-cycle 50%
Output enable or disable time		—	—	2	cycle	—
Output to output skew	t_{OOSK}	—	—	27	ps	—
Device-to-device output skew	t_{DOOSK}	—	—	1.6	ns	—
Input to output delay	t_{IOD}	1.15	2.09	2.54	ns	$V_{DD} = 3.3V$
		1.57	2.27	2.77	ns	$V_{DD} = 2.5V$
Input multiplexer isolation	ISO	75	—	—	dB	Tested with 125 MHz clocks

Note 1: Values are over recommended operating conditions. Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$). Load 50 Ω to $V_{DDO}/2$.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

TABLE 3.7: LVCMOS OUTPUT ADDITIVE JITTER AND PHASE NOISE (Note 1)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
System level additive jitter, Note 2		—	17	—	fs – RMS	$V_{DD} = 3.3V$, $V_{DDO} = 3.3V$ $f_{in} = 125\text{ MHz}$, single ended input
		—	31	—	fs – RMS	$V_{DD} = 2.5V$, $V_{DDO} = 1.5V$ to $2.5V$ $f_{in} = 125\text{ MHz}$, single ended input
		—	22	—	fs – RMS	$V_{DD} = 3.3V$, $V_{DDO} = 3.3V$ $f_{in} = 125\text{ MHz}$, differential input
		—	37	—	fs – RMS	$V_{DD} = 2.5V$, $V_{DDO} = 1.5V$ to $2.5V$ $f_{in} = 125\text{ MHz}$, differential input
Additive jitter, Note 3, Note 4		—	45.18	93.11	fs – RMS	$V_{DD} = 3.3V$, $V_{DDO} = 3.3V$ $f_{in} = 125\text{ MHz}$, single ended input
		—	80.46	126.92	fs – RMS	$V_{DD} = 2.5V$, $V_{DDO} = 1.5V$ to $2.5V$ $f_{in} = 125\text{ MHz}$, single ended input
		—	39.95	68.98	fs – RMS	$V_{DD} = 3.3V$, $V_{DDO} = 3.3V$ $f_{in} = 125\text{ MHz}$, differential input
		—	67.18	117.26	fs – RMS	$V_{DD} = 2.5V$, $V_{DDO} = 1.5V$ to $2.5V$ $f_{in} = 125\text{ MHz}$, differential input
Phase noise floor ($V_{DD} = 3.3V$, $V_{DDO} = 3.3V$)		—	–145.08	–138.67	dBc/Hz	@10 kHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–152.46	–145.82	dBc/Hz	@100 kHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–160.67	–155.66	dBc/Hz	@1 MHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–162.66	–160.55	dBc/Hz	@10 MHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–162.71	–160.19	dBc/Hz	@20 MHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–145.34	–137.83	dBc/Hz	@10 kHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–152.60	–146.93	dBc/Hz	@100 kHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–161.06	–156.99	dBc/Hz	@1 MHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–163.22	–160.84	dBc/Hz	@10 MHz, $f_{in} = 125\text{ MHz}$, single ended input
		—	–163.38	–161.42	dBc/Hz	@20 MHz, $f_{in} = 125\text{ MHz}$, single ended input

Note 1: Values are over recommended operating conditions. Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$).

Note 2: System level additive jitter is calculated as $J_{RMS_SYS_AJ} = J_{RMS_OUT} - J_{RMS_IN}$

Note 3: Additive jitter is calculated as $J_{RMS_AJ} = \text{sqrt}(J_{RMS_OUT} - J_{RMS_IN})$. Where jitter is integrated in 12 KHz to 20 MHz band.

Note 4: Tester measures jitter at 156.25 MHz. Since this frequency won't appear in the data sheet, it should be removed from the PPGT. Data sheet jitter is guaranteed by lab char. The ATE jitter measurement will be used to screen outliers only, with limits based on ATE distribution.

Ten LVCMOS Output Low Additive Jitter Fanout Buffer

TABLE 3.7: LVCMOS OUTPUT ADDITIVE JITTER AND PHASE NOISE (Note 1) (CONTINUED)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
Phase noise floor (VDD = 2.5V, VDDO = 2.5V)		—	-139.93	-134.59	dBc/Hz	@10 kHz, $f_{in} = 125$ MHz, single ended input
		—	-147.22	-144.21	dBc/Hz	@100 kHz, $f_{in} = 125$ MHz, single ended input
		—	-157.11	-154.78	dBc/Hz	@1 MHz, $f_{in} = 125$ MHz, single ended input
		—	-160.58	-158.21	dBc/Hz	@10 MHz, $f_{in} = 125$ MHz, single ended input
		—	-160.78	-158.19	dBc/Hz	@20 MHz, $f_{in} = 125$ MHz, single ended input
		—	-141.69	-134.26	dBc/Hz	@10 kHz, $f_{in} = 125$ MHz, single ended input
		—	-149.19	-144.73	dBc/Hz	@100 kHz, $f_{in} = 125$ MHz, single ended input
		—	-158.66	-156.22	dBc/Hz	@1 MHz, $f_{in} = 125$ MHz, single ended input
		—	-161.60	-159.32	dBc/Hz	@10 MHz, $f_{in} = 125$ MHz, single ended input
		—	-161.85	-159.36	dBc/Hz	@20 MHz, $f_{in} = 125$ MHz, single ended input

Note 1: Values are over recommended operating conditions. Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$).

Note 2: System level additive jitter is calculated as $J_{RMS_SYS_AJ} = J_{RMS_OUT} - J_{RMS_IN}$

Note 3: Additive jitter is calculated as $J_{RMS_AJ} = \sqrt{J_{RMS_OUT} - J_{RMS_IN}}$. Where jitter is integrated in 12 KHz to 20 MHz band.

Note 4: Tester measures jitter at 156.25 MHz. Since this frequency won't appear in the data sheet, it should be removed from the PPGT. Data sheet jitter is guaranteed by lab char. The ATE jitter measurement will be used to screen outliers only, with limits based on ATE distribution.

TABLE 3.8: LVCMOS OUTPUT JITTER PHASE NOISE WITH 25 MHZ XTAL (NOTE 1)

Characteristics	Symbol	Min.	Typ.	Max.	Units.	Notes.
Jitter RMS in 12 kHz to 20 MHz band		—	72.63	—	fs	$V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	87.59	—	fs	$V_{DD} = 2.5V, V_{DDO} = 2.5V$
Phase noise floor		—	-75.96	—	dBc/Hz	@10 Hz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-107.50	—	dBc/Hz	@100 Hz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-132.34	—	dBc/Hz	@1 kHz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-157.36	—	dBc/Hz	@10 kHz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-165.82	—	dBc/Hz	@100 kHz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-168.85	—	dBc/Hz	@1 MHz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-168.88	—	dBc/Hz	@5 MHz, $V_{DD} = 3.3V, V_{DDO} = 3.3V$
		—	-70.52	—	dBc/Hz	@10 Hz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-102.60	—	dBc/Hz	@100 Hz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-129.14	—	dBc/Hz	@1 kHz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-153.93	—	dBc/Hz	@10 kHz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-164.00	—	dBc/Hz	@100 kHz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-167.34	—	dBc/Hz	@1 MHz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$
		—	-167.41	—	dBc/Hz	@5 MHz, $V_{DD} = 2.5V, V_{DDO} = 2.5V$

Note 1: Values are over recommended operating conditions. Values are over all two power supply modes ($V_{DD} = 3.3V$ and $V_{DD} = 2.5V$). XTAL frequency is 25 MHz.

TABLE 3.9: 5 MM × 5 MM VQFN PACKAGE THERMAL PROPERTIES

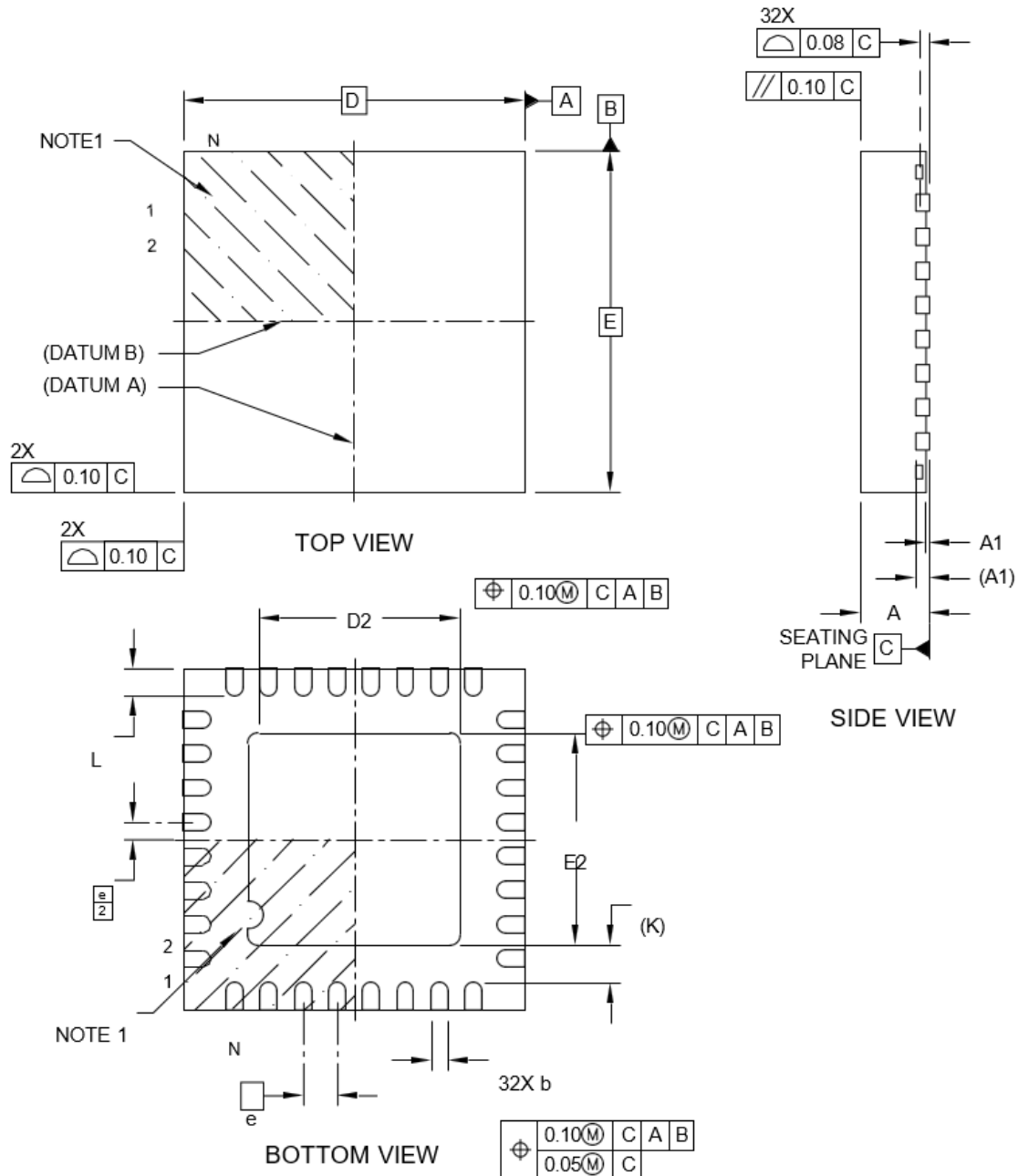
Parameter	Symbol	Conditions.	Value.	Units.
Maximum ambient temperature	T_A	—	85	°C
Maximum junction temperature	$T_{J(MAX)}$	—	125	°C
Junction to ambient thermal resistance, Note 1	θ_{JA}	Still air	26.8	°C/W
		1 m/s airflow	21.8	°C/W
		2.5 m/s airflow	19.9	°C/W
Junction to board thermal resistance	θ_{JB}	—	10.8	°C/W
Junction to case thermal resistance	θ_{JC}	—	19.5	°C/W
Junction to pad thermal resistance, Note 2	θ_{JP}	Still air	6.5	°C/W
Junction to top-center thermal characterization	ψ_{JT}	Still air	0.6	°C/W

Note 1: θ_{JA} is the thermal resistance from junction to ambient when the package is mounted on a 4-layer JEDEC standard test board and dissipating maximum power.

Note 2: θ_{JP} is the thermal resistance from junction to the center exposed pad on the bottom of the package.

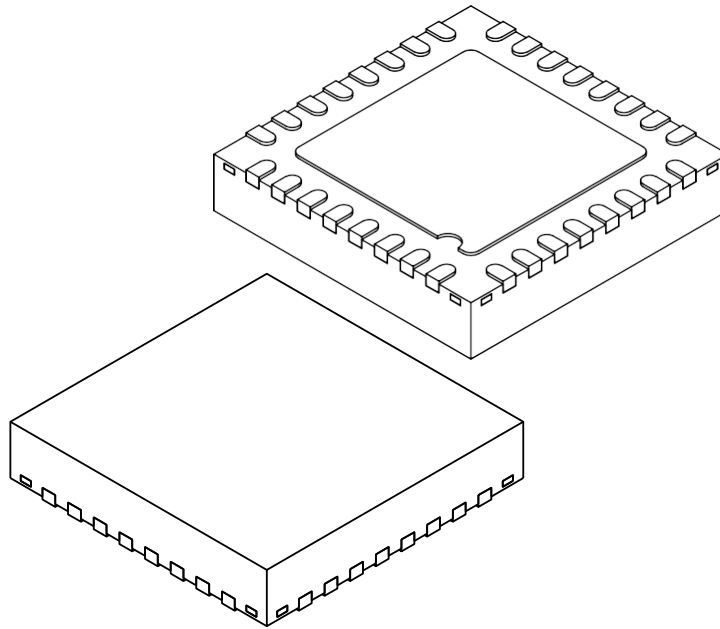
4.0 PACKAGE OUTLINE

32-Lead 5 mm x 5 mm VQFN Package Outline and Recommended Land Pattern



Ten LVCMOS Output Low Additive Jitter Fanout Buffer

32-Lead 5 mm x 5 mm VQFN Package Outline and Recommended Land Pattern



Dimension Limits	Units	Millimeters		
		MIN	NOM	MAX
Number of Terminals	N	32		
Pitch	e	0.50 BSC		
Overall Height	A	0.80	0.90	1.00
Standoff	A1	0.00	0.02	0.05
Terminal Thickness	A3	0.20 REF		
Overall Length	D	5.00 BSC		
Exposed Pad Length	D2	3.00	3.10	3.20
Overall Width	E	5.00 BSC		
Exposed Pad Width	E2	3.00	3.10	3.20
Terminal Width	b	0.20	0.25	0.30
Terminal Length	L	0.35	0.40	0.45
Terminal-to-Exposed-Pad	K	0.20	-	-

Note 1: Pin 1 visual index feature may vary, but must be located within the hatched area.

Note 2: Package is saw singulated

Note 3: Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

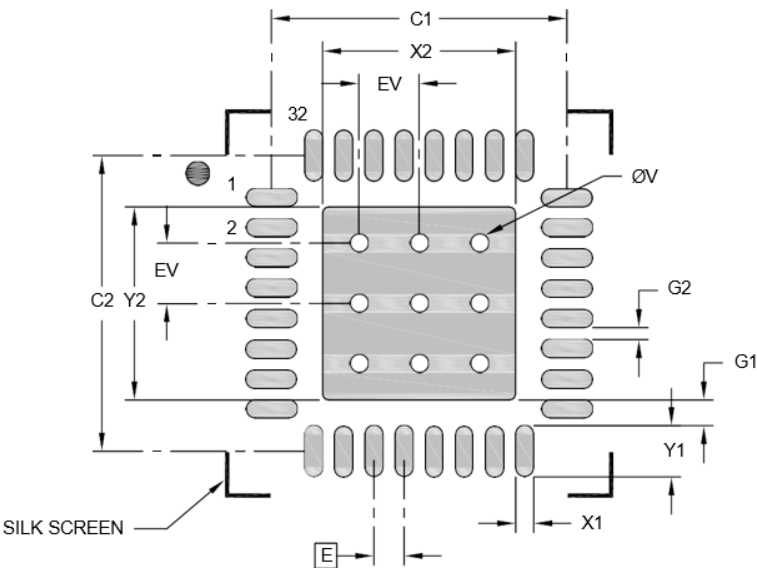
REF: Reference Dimension, usually without tolerance, for information purposes only.

ABFB10CB1A series

Ten LVCMOS Output Low Additive Jitter Fanout Buffer



32-Lead 5 mm x 5 mm VQFN Package Outline and Recommended Land Pattern



RECOMMENDED LAND PATTERN

		Units	Millimeters		
Dimension Limits			MIN	NOM	MAX
Contact Pitch	E		0.50 BSC		
Optional Center Pad Width	X2				3.20
Optional Center Pad Length	Y2				3.20
Contact Pad Spacing	C1			4.90	
Contact Pad Spacing	C2			4.90	
Contact Pad Width (X32)	X1				0.30
Contact Pad Length (X32)	Y1				0.85
Contact Pad to Center Pad (X32)	G1		0.23		
Contact Pad to Contact Pad (X28)	G2		0.20		
Thermal Via Diameter	V			0.30	
Thermal Via Pitch	EV			1.00	

Note 1: Dimensioning and tolerancing per ASME Y14.5M
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Note 2: For best soldering results, thermal vias, if used, should be filled or tented to avoid solder loss during reflow process